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BF556A; BF556B; BF556C

N-channel silicon junction field-effect transistors

Rev. 4 — 15 September 2011

Product data sheet

1. Product profile

1.1 General description

N-channel symmetrical silicon junction field-effect transistors in a SOT23 package.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

- Low leakage level (typ. 500 fA)
- High gain
- Low cut-off voltage.

1.3 Applications

- Impedance converters in e.g. electret microphones and infrared detectors
- VHF amplifiers in oscillators and mixers.

1.4 Quick reference data

Table 1. Quick reference data

Parameter	Conditions	Min	Тур	Max	Unit
drain-source voltage (DC)		-	-	±30	V
gate-source cut-off voltage	$I_D = 200 \mu A;$ $V_{DS} = 15 V$	-0.5	-	-7.5	V
drain current	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$				
	BF556A	3	-	7	mA
	BF556B	6	-	13	mA
	BF556C	11	-	18	mA
total power dissipation	$T_{amb} \le 25 ^{\circ}C$	-	-	250	mW
forward transfer admittance	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	4.5	-	-	mS
	drain-source voltage (DC) gate-source cut-off voltage drain current total power dissipation forward transfer	$\begin{array}{ll} \text{drain-source} \\ \text{voltage (DC)} \\ \text{gate-source cut-off} \\ \text{voltage} & V_{DS} = 200 \ \mu\text{A}; \\ V_{DS} = 15 \ \text{V} \\ \\ \text{drain current} & V_{GS} = 0 \ \text{V}; \ \text{V}_{DS} = 15 \ \text{V} \\ \\ \text{BF556A} \\ \\ \text{BF556B} \\ \\ \text{BF556C} \\ \\ \text{total power} \\ \text{dissipation} & T_{amb} \leq 25 \ ^{\circ}\text{C} \\ \\ \text{forward transfer} & V_{GS} = 0 \ \text{V}; \ \text{V}_{DS} = 15 \ \text{V} \\ \end{array}$	$\begin{array}{c} \text{drain-source} \\ \text{voltage (DC)} \\ \text{gate-source cut-off} \\ \text{voltage} \\ \end{array} \begin{array}{c} I_D = 200 \ \mu \text{A}; \\ V_{DS} = 15 \ \text{V} \\ \end{array} \begin{array}{c} -0.5 \\ \text{V}_{DS} = 15 \ \text{V} \\ \end{array}$ $\begin{array}{c} \text{drain current} \\ \end{array} \begin{array}{c} V_{GS} = 0 \ \text{V}; \ \text{V}_{DS} = 15 \ \text{V} \\ \end{array} \begin{array}{c} BF556A \qquad 3 \\ BF556B \qquad 6 \\ BF556C \qquad 11 \\ \end{array}$ $\begin{array}{c} \text{total power} \\ \text{dissipation} \\ \end{array} \begin{array}{c} T_{amb} \leq 25 \ ^{\circ}\text{C} \\ \end{array} \begin{array}{c} - \\ \text{dissipation} \\ \end{array}$	$\begin{array}{c} \text{drain-source} \\ \text{voltage (DC)} \\ \text{gate-source cut-off} \\ \text{voltage} \\ \end{array} \begin{array}{c} I_D = 200 \ \mu A; \\ V_{DS} = 15 \ V \\ \\ \text{drain current} \\ \end{array} \begin{array}{c} V_{GS} = 0 \ V; \ V_{DS} = 15 \ V \\ \\ \hline BF556A & 3 & - \\ \hline BF556B & 6 & - \\ \hline BF556C & 11 & - \\ \\ \text{total power dissipation} \\ \end{array} \begin{array}{c} T_{amb} \leq 25 \ ^{\circ}C \\ \\ \text{forward transfer} \\ \end{array} \begin{array}{c} - \\ V_{GS} = 0 \ V; \ V_{DS} = 15 \ V \\ \end{array} \begin{array}{c} - \\ \end{array} \begin{array}{$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	source (s)		
2	drain (d)		g → d s
3	gate (g)	1 - 2	sym054

3. Ordering information

Table 3. Ordering information

	3 · · · · · · · · · · · · · · · · · · ·					
Type number	Package	kage				
	Name	Description	Version			
BF556A	-	plastic surface mounted package; 3 leads	SOT23			
BF556B						
BF556C						

4. Marking

Table 4. Marking

Type number	Marking code[1]
BF556A	24*
BF556B	25*
BF556C	26*

^{[1] * =} p: made in Hong Kong.

^{* =} t: made in Malaysia.

^{* =} W: made in China.

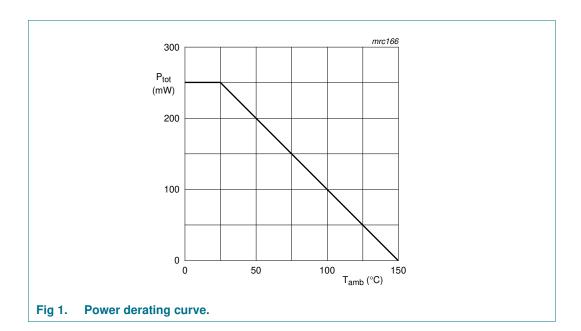
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)		-	±30	V
V_{GSO}	gate-source voltage	open drain	-	-30	V
V_{GDO}	gate-drain voltage (DC)	open source	-	-30	V
I _G	forward gate current (DC)		-	10	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> -	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

[1] Device mounted on an FR4 printed-circuit board, maximum lead length 4 mm; mounting pad for the drain lead 10 mm².



6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient		<u>[1]</u> 500	K/W

^[1] Device mounted on an FR4 printed-circuit board, maximum lead length 4 mm; mounting pad for the drain lead 10 mm².

7. Static characteristics

Table 7. Static characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)GSS}$	gate-source breakdown voltage	$I_G=-1~\mu A;~V_{DS}=0~V$	-30	-	-	V
V_{GSoff}	gate-source cut-off voltage	$I_D = 200 \ \mu A; \ V_{DS} = 15 \ V$	-0.5	-	-7.5	V
I _{DSS} drain current		$V_{GS} = 0 \ V; \ V_{DS} = 15 \ V$				
		BF556A	3	-	7	mA
		BF556B	6	-	13	mA
		BF556C	11	-	18	mA
I _{GSS}	gate-source leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}$	-	-0.5	-5000	pА
y _{fs}	forward transfer admittance	$V_{GS} = 0 \ V; \ V_{DS} = 15 \ V$	4.5	-	-	mS
y _{os}	common source output admittance	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}$	-	40	-	μS

8. Dynamic characteristics

Table 8. Dynamic characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{iss} input capacitance	input capacitance	$V_{DS} = 15 \text{ V}; f = 1 \text{ MHz}$				
		$V_{GS} = -10 \text{ V}$	-	1.7	-	pF
		V _{GS} = 0 V	-	3	-	pF
C _{rss} reverse transfer capacitance	reverse transfer capacitance	$V_{DS} = 15 \text{ V}; f = 1 \text{ MHz}$				
		$V_{GS} = -10 \text{ V}$	-	8.0	-	pF
		V _{GS} = 0 V	-	0.9	-	pF
g _{is} common source input conductance	$V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}$					
	conductance	f = 100 MHz	-	15	-	μS
	f = 450 MHz	-	300	-	μS	
g _{fs} common source transfer conductance	$V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}$					
	conductance	f = 100 MHz	-	2	-	mS
	f = 450 MHz	-	1.8	-	mS	
g _{rs} common source reverse	$V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}$	-	-6	-	μS	
	conductance	f = 100 MHz	-	-6	-	μS
		f = 450 MHz	-	-40	-	μS
g _{os}	common source output	$V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}$				
	conductance	f = 100 MHz	-	30	-	μS
		f = 450 MHz	-	60	-	μS
V _n	equivalent input noise voltage	$V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA};$ f = 100 Hz	-	40	-	nV/√Hz

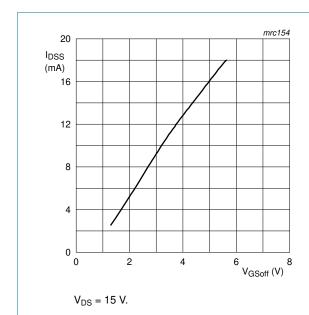
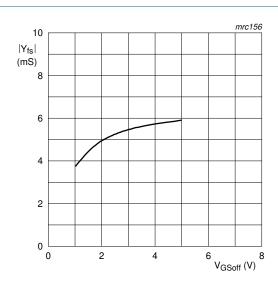


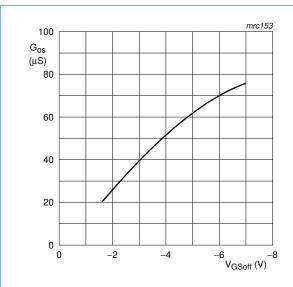
Fig 2. Drain current as a function of gate-source cut-off voltage; typical values.



 $V_{DS} = 15 \text{ V}; I_D = 1 \mu A.$

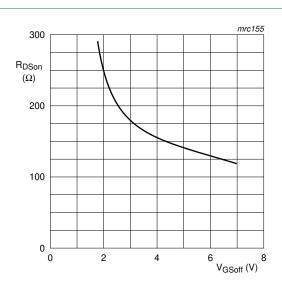
Fig 3. Forward transfer admittance as a function of gate-source cut-off voltage; typical values.

BF556A_BF556B_BF556C



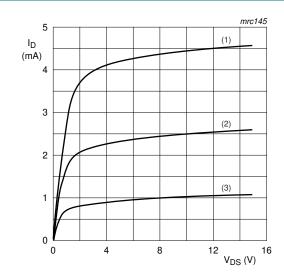
 $V_{DS} = 15 V.$

Fig 4. Common-source output conductance as a function of gate-source cut-off voltage; typical values.



 $V_{DS} = 100 \text{ mV}$; $V_{GS} = 0 \text{ V}$.

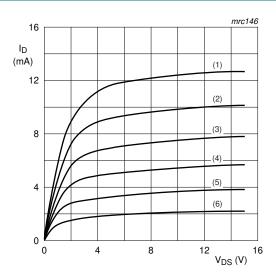
Fig 5. Drain-source on-state resistance as a function of gate-source cut-off voltage; typical values.



BF556A

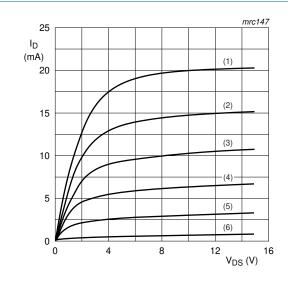
- (1) $V_{GS} = 0 V$.
- (2) $V_{GS} = -0.5 \text{ V}.$
- (3) $V_{GS} = -1.0 \text{ V}.$

Fig 6. Typical output characteristics.



BF556B

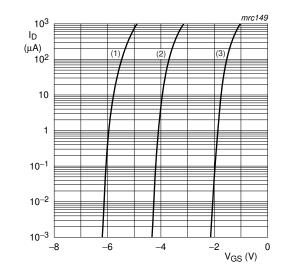
- (1) $V_{GS} = 0 \text{ V}.$
- (2) $V_{GS} = -0.5 \text{ V}.$
- (3) $V_{GS} = -1.0 \text{ V}.$
- (4) $V_{GS} = -1.5 \text{ V}.$
- (5) $V_{GS} = -2.0 \text{ V}.$ (6) $V_{GS} = -2.5 \text{ V}.$
- Fig 7. Typical output characteristics.



BF556C

- (1) $V_{GS} = 0 V$.
- (2) $V_{GS} = -1.0 \text{ V}.$
- (3) $V_{GS} = -2.0 \text{ V}.$
- (4) $V_{GS} = -3.0 \text{ V}.$
- (5) $V_{GS} = -4.0 \text{ V}.$
- (6) $V_{GS} = -5.0 \text{ V}.$

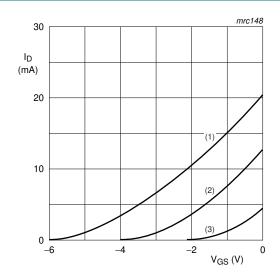
Fig 8. Typical output characteristics.



 $V_{DS} = 15 \text{ V}.$

- (1) BF556C.
- (2) BF556B.
- (3) BF556A.

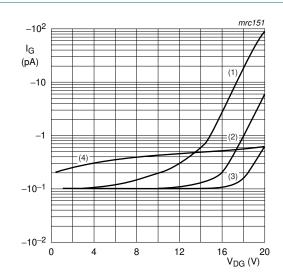
Fig 10. Drain current as a function of gate-source voltage; typical values.



 $V_{DS} = 15 \text{ V}.$

- (1) BF556C.
- (2) BF556B.
- (3) BF556A.

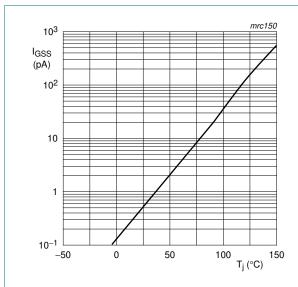
Fig 9. Typical input characteristics.



 $I_D = 10$ mA only for BF556B and BF556C.

- (1) $I_D = 10 \text{ mA}.$
- (2) $I_D = 1 \text{ mA}.$
- (3) $I_D = 0.1 \text{ mA}.$
- (4) I_{GSS}.

Fig 11. Gate current as a function of drain-gate voltage; typical values.



 $V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}.$

Fig 12. Gate current as a function of junction temperature; typical values.

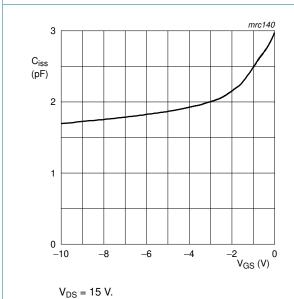
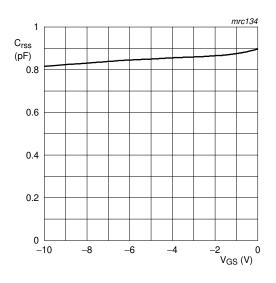
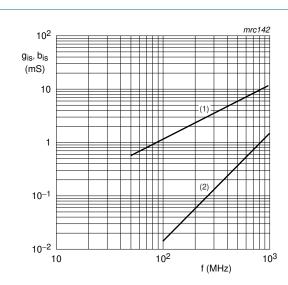


Fig 14. Input capacitance; typical values.



 $V_{DS} = 15 V.$

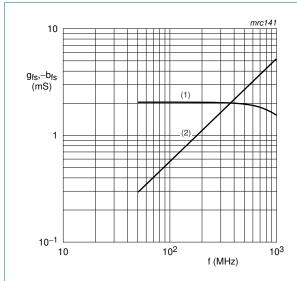
Fig 13. Reverse transfer capacitance; typical values.



$$V_{DS}$$
 = 10 V; I_D = 1 mA; T_{amb} = 25 °C.

- (1) b_{is}.
- (2) g_{is}.

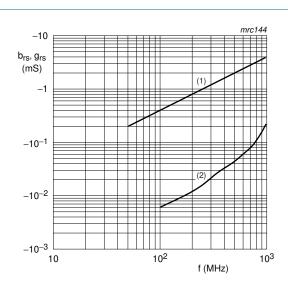
Fig 15. Common-source input admittance; typical values.



 V_{DS} = 10 V; I_D = 1 mA; T_{amb} = 25 °C.

- (1) g_{fs}
- (2) -b_{fs}.

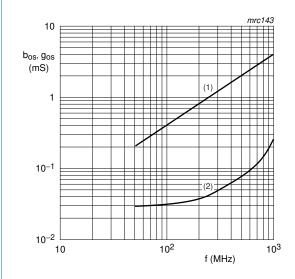
Fig 16. Common-source transfer admittance; typical values.



 $V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}; T_{amb} = 25 \text{ °C}.$

- b_{rs}.
- (2) g_{rs}.

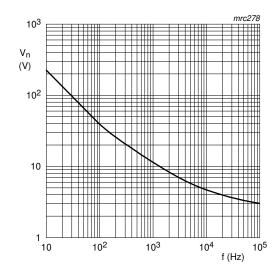
Fig 17. Common-source reverse admittance; typical values.



 V_{DS} = 10 V; I_D = 1 mA; T_{amb} = 25 °C.

- (1) b_{os}.
- (2) g_{os}.

Fig 18. Common-source output admittance;typical values.



 $V_{DS} = 10 \text{ V}; I_D = 1 \text{ mA}.$

Fig 19. Equivalent noise voltage as a function of frequency.

9. Package outline

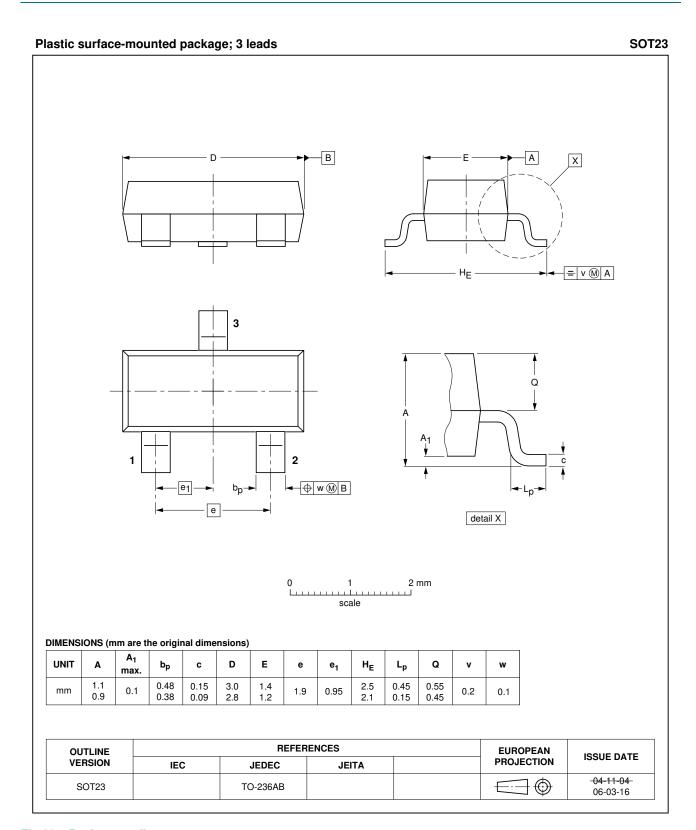


Fig 20. Package outline.

10. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BF556A_BF556B_BF556C v.4	20110915	Product data sheet	-	BF556A_BF556B_BF556C v.3
Modifications:	guidelines o • Legal texts	of NXP Semiconductors	ne new company r	comply with the new identity name where appropriate. atest version.
BF556A_BF556B_BF556C v.3 (9397 750 13393)		Product data sheet	-	BF556A-B-C v.2
BF556A-B-C v.2	19960729	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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BF556A_BF556B_BF556C

BF556A; BF556B; BF556C

N-channel silicon junction field-effect transistors

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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12. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.